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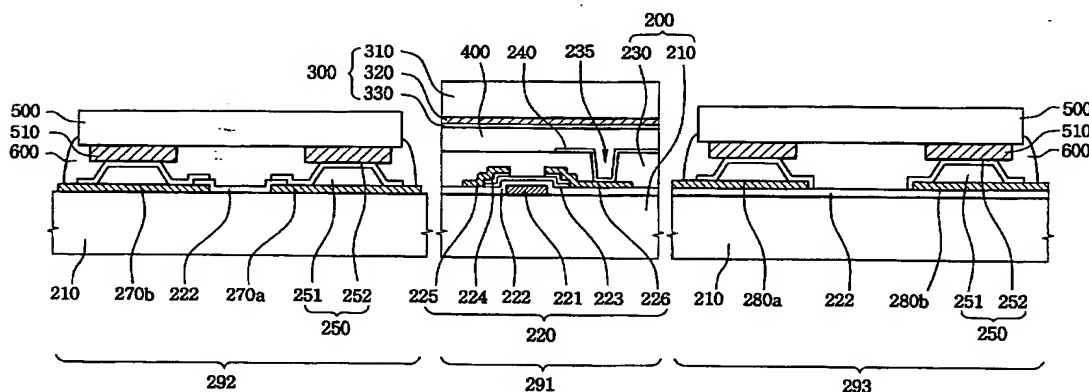
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(54) Title: THIN FILM TRANSISTOR SUBSTRATE, METHOD OF MANUFACTURING THE SAME, LIQUID CRYSTAL DIS-  
PLAY APPARATUS HAVING THE SAME AND METHOD OF MANUFACTURING THE LIQUID CRYSTAL DISPLAY AP-  
PARATUS



(57) Abstract: A conductive bump including a plurality of protrusion members (251) and a conductive layer (252) formed on the protrusion members is disposed on a TFT substrate (200). Each of the protrusion members is disposed on an electrode pad (270y, b) in a pad region (292, 293) of the TFT substrate, and the conductive layer is electrically connected to the electrode pad. A non-conductive resin (600) is disposed on the conductive bump, and a driving IC (500) is thermally compressed on the conductive bump. Therefore, the electrical contact characteristic between the driving IC and the electrode pad is improved.